



SOT-23 Plastic-Encapsulate Transistors

BCW60C TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.25 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.1 A

Collector-base voltage

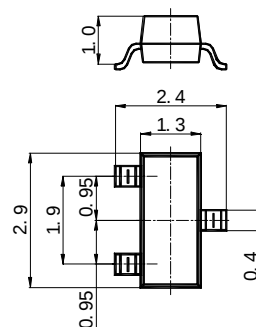
$V_{(BR)CBO}$: 32 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	32		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=32V, I_E=0$		0.02	μA
Collector cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$		0.02	μA
DC current gain	h_{FE1}	$V_{CE}=5V, I_C=10\mu A$	40		
	h_{FE2}	$V_{CE}=5V, I_C=2mA$	250	460	
	h_{FE3}	$V_{CE}=5V, I_C=50mA$	100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=0.25mA$		0.35	V
		$I_C=50mA, I_B=1.25mA$		0.55	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=0.25mA$		0.85	V
		$I_C=50mA, I_B=1.25mA$		1.05	V
Base-emitter voltage	V_{BE}	$V_{CE}=5V, I_C=2mA$	0.55	0.75	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA, f=100MHz$	100		MHz
Output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		5	pF

Marking

AC